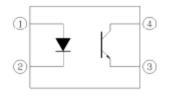
QT BRIGHTEK

4-PIN DC INPUT OPTOCOUPLER

Feature:

- Halogen Free
- High Isolation voltage between input and output (Viso = 5000V rms)
- Creepage distance > 7.62mm
- Operating Temperature up to 100 °C
- Available in Tube or Tape and reel
- Available with standard DIP-4, Wide lead bend, and SMD lead bend options.
- Conventional black housing package

Schematic:



Pin Configuration

- 1. Anode
- 2. Cathode
- 3. Emitter
- 4. Collector

Certification & Compliance:

- Pb free and RoHS Compliant
- UL recognized (File # E338132)
- VDE recognized (File # 40030457)

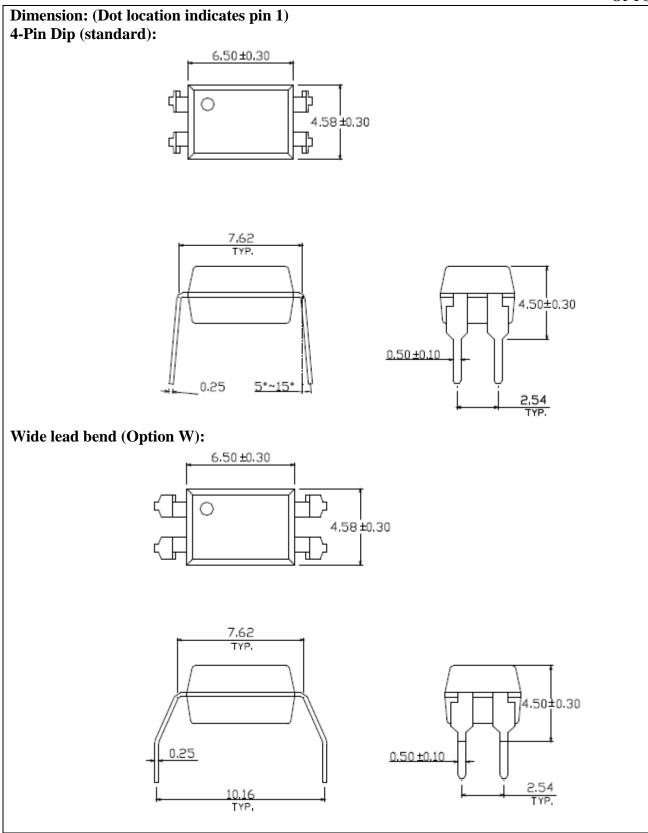


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QT BRIGHTEK

Q817 series

4-PIN DC INPUT OPTOCOUPLER



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QT BRIGHTEK

SMD lead bend (Option S): 6,50±0,30 tÞ 5 0 1,30 4.58±0.30 d, ЦЪ 7.62 TYP. 3 50 ±0.30 4.30 ±0.30 0.6 MIN 0.25 2.54 TYP. 10,30 MAX All Dimensions are in mm Tolerance = +/- 0.1mm

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Absolute Maximum Rating

| Symbol | Parameter | Rating | Units |
|------------------|--|----------------|-------|
| T _{STG} | Storage Temperature | -55 ~ 150 | ٥C |
| T _{OPR} | Operating Temperature | -55 ~ 100 | °C |
| T _{SOL} | Lead Solder Temperature | 260 for 10 sec | °C |
| P _{TOT} | Total Power Dissipation | 200 | mW |
| EMITTER | | | |
| I _F | Continuous Forward Current | 50 | mA |
| V _R | Reverse Voltage | 6 | V |
| D. | Power Dissipation | 70 | mW |
| PD | Power Dissipation Derated above 100°C | 2.9 | mW/ºC |
| DETECTOR | 8 | | |
| V _{CEO} | Collector–Emitter Voltage | 80 | V |
| V _{ECO} | Emitter-Collector Voltage | 7 | V |
| I _C | Continuous Collector Current | 50 | mA |
| Pc | Collector Power Dissipation | 150 | mW |
| ГC | Collector Power Dissipation Derated above80 °C | 5.8 | mW/ºC |

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Electrical Characteristic (T_A=25 °C)

Emitter

| Symbol | Characteristic | Device Test Condition | | | Unit | | |
|----------------|-------------------|-----------------------|----------------------|-----|------|-----|------|
| Symbol | Characteristic | Device | | Min | Тур | Max | Onit |
| V _F | Forward Voltage | | $I_F = 20 \text{mA}$ | - | 1.2 | 1.4 | V |
| I _R | Reverse Current | Q817 | $V_R = 4V$ | - | - | 10 | μA |
| Ct | Input Capacitance | | V = 0, f = 1 kHz | - | 30 | 250 | pF |

Detector

| Symbol | Characteristic | Device | Device Test Condition | | Range | | |
|-------------------|--|--------|--|-----|-------|-----|------|
| Symbol | Characteristic | Device | Test Condition | Min | Тур | Max | Unit |
| I _{CEO} | Collector-Emitter Dark current | | V _{CE} =20V, I _F =0mA | - | - | 100 | nA |
| BV _{CEO} | Collector-Emitter breakdown voltage | Q817 | $I_{\rm C} = 0.1 \mathrm{mA}$ | 80 | - | - | V |
| BV _{ECO} | Emitter-Collector breakdown voltage | | I _E = 0.1mA | 7 | - | - | V |

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DC Transfer Characteristic:

| | | Device | Bin | Test Condition | F | Range | | Unit |
|----------------------|-----------------------|--------|------|---|-----|-------|-----|-------|
| | | Device | DILI | Test Condition | Min | Тур | Max | Offic |
| | | | - | | 50 | - | 600 | |
| Symbol | Characteristic | | Α | | 80 | - | 160 | |
| | | Q817 | В | I _F =5mA, V _{CE} =5V | 130 | - | 260 | % |
| | | | С | | 200 | - | 400 | |
| | | | D | | 400 | - | 600 | |
| | Collector- Emitter | | | I _F =20mA, | | 0.1 | 0.2 | V |
| V _{CE(Sat)} | saturation voltage | | | I _F =20mA, I _C = 1mA | - | 0.1 | 0.2 | V |

AC Characteristic

| Symbol | Characteristic | Dovice | Bin | Test Condition | F | Range | | Unit |
|----------------|----------------|--------|------|---|-----|-------|-----|------|
| Symbol | Characteristic | Device | DILI | Test Condition | Min | Тур | Max | Unit |
| t _r | Rise time | | | V _{CE} = 2V, I _C = 2mA | - | 6 | 18 | |
| t _f | Fall time | | | $R_L = 100\Omega$ | - | 8 | 18 | μs |

Isolation Characteristic

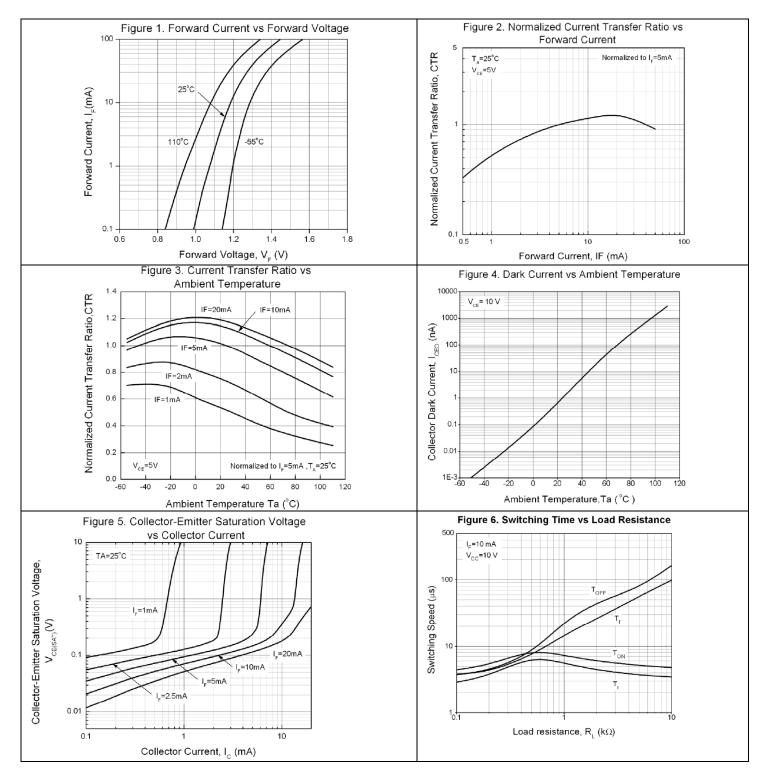
| Symbol | Characteristic | Device | Bin | Test Condition | F | Range | | Unit |
|------------------|----------------|--------|------|------------------------------|--------------------|-------|-----|--------|
| Symbol | Characteristic | Device | DILI | Test Condition | Min | Тур | Max | Unit |
| R _{ISO} | Isolation | | | V _{IO} =500Vdc, | 5X10 ¹⁰ | _ | _ | Ω |
| riso | Resistance | | | 40-60% R.H | 5710 | - | - | 12 |
| CISO | Isolation | | | V _{IO} =0, f = 1MHz | _ | 0.6 | 1.0 | рF |
| CISO | Capacitance | | | | - | 0.0 | 1.0 | ρг |
| V | Isolation | | | f=60Hz, t=1min, | 5000 | | | V rms |
| V _{ISO} | Voltage | | | I _{I-O} ≤ 2 μA | 5000 | - | - | v 1115 |

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Q817 series

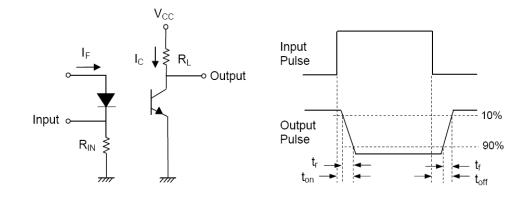
Characteristic Curves:



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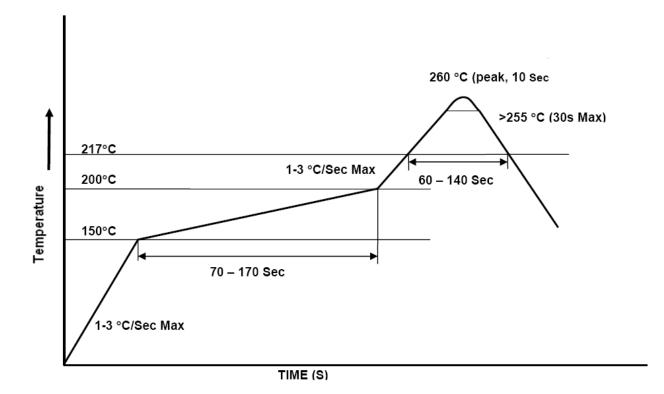
Test Circuit for Response Time:

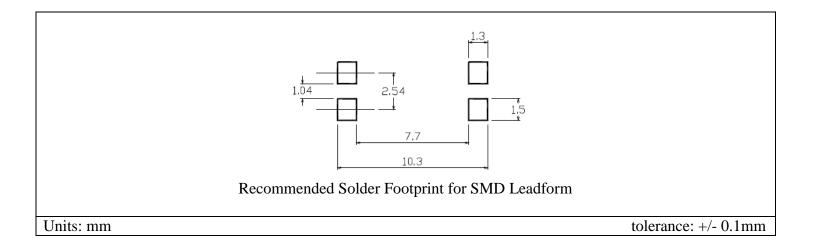


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Solder Profile & Footprint:

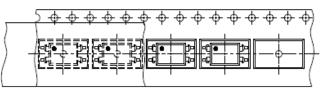


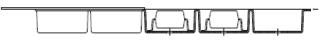


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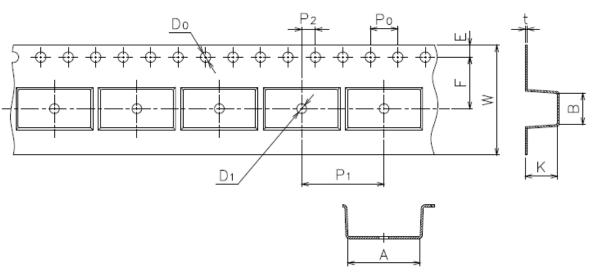


Packing & Labeling: Tape Dimension:





Direction of feed from reel

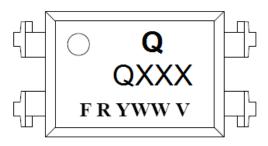


| Dimension No. | A | в | Do | D1 | E | F |
|---------------|----------|----------|---------|----------|-------------------|----------|
| Dimension(mm) | 10.4±0.1 | 4.55±0.1 | 1.5±0.1 | 1.5±0.05 | 1.75±0.1 | 7.5±0.1 |
| Dimension No. | Po | P1 | P2 | t | w | к |
| Dimension(mm) | 4.0±0.1 | 12.0±0.1 | 2.0±0.1 | 0.33±0.1 | 16.0+0.3/ -0.1 | 4.55±0.1 |

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Device Marking:



Q = QT-Brightek Corporation QXXX = Device Part NumberF = Country of OriginR = Binning OptionY = YearWW = WeekV = VDE Option

Ordering Information:

| Part | Orderable Part | Options | Description | Quantity per |
|--------|----------------|---------|--|----------------|
| Number | Number | | | packing |
| | Q817X | None | Standard 4pin DIP | 100pcs / Tube |
| | Q817XV | None | Standard 4 pin Dip + With VDE marking | 100pcs / Tube |
| | Q817XW | W | Wide lead bend (0.4 inch spacing) | 100pcs / Tube |
| Q817 | Q817XWV | W | Wide lead bend (0.4 inch spacing) + VDE marking | 100pcs / Tube |
| | Q817XSTA | S | SMD lead form with tape and reel option | 2000pcs / reel |
| | Q817XSTAV | S | SMD lead form with tape and reel option + VDE marking | 2000pcs / reel |

X – Note is CTR Binning.

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Revision History:

| Description: | Revision # | Revision Date |
|--|------------|---------------|
| Initial release | 1.0 | 4/12/2010 |
| Add CTR rank binning option and VDE number | 1.1 | 7/28/2010 |
| Feature, certification & compliance and ordering information updates | 1.2 | 02/01/2011 |
| | | |
| | | |

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.

2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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